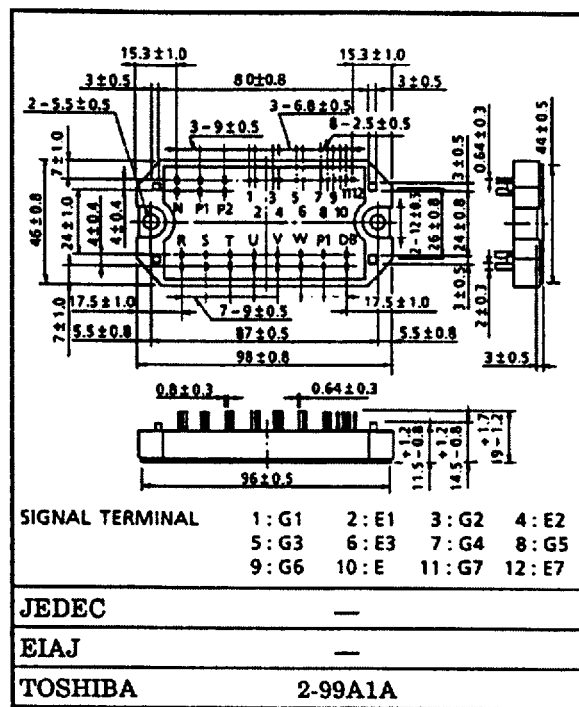


Unit in mm

High Power Switching Applications

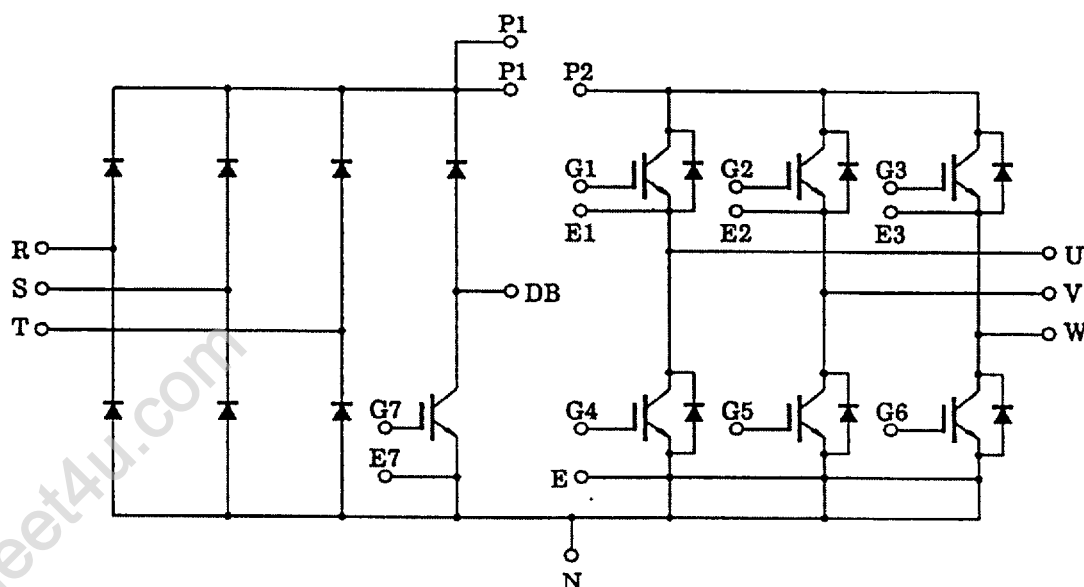
Motor Control Applications

- Integrates Inverter, Converter and Brake Power Circuits in One Package.
- Output (Inverter Stage)
 - : 3 ϕ 15A/1200V High Speed Type IGBT
 - $V_{CE(sat)}$ = 4.00V (Max.)
 - t_f = 0.30 μ s (Max.)
 - t_{rr} = 0.15 μ s (Max.)
- Input (Converter Stage)
 - : 3 ϕ 15A/1600V Silicon Rectifier
 - V_F = 1.20V (Max.)
- Brake Stage
 - : 8A/1200V IGBT & 8A/1200V FRD
- The Electrodes are Isolated from Case.



Weight : 175g

Equivalent Circuit



The information contained here is subject to change without notice.

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Maximum Ratings (Ta = 25°C)

STAGE		CHARACTERISTIC		SYMBOL	RATINGS	UNIT
Inverter		Collector-Emitter Voltage		V_{CES}	1200	V
		Gate-Emitter Voltage		V_{GES}	±20	V
		Collector Current	DC	I_C	15	A
			1ms	I_{CP}	30	
		Forward Current	DC	I_F	15	A
			1ms	I_{FM}	30	
		Collector Power Dissipation (Tc = 25°C)		P_C	125	W
Converter		Repetitive Peak Reverse Voltage		V_{RRM}	1600	V
		Average Output Rectified Current		I_O	15	A
		Peak One Cycle Surge Forward Current (50Hz, Non-Repetitive)		I_{FSM}	250	A
Brake	IGBT	Collector-Emitter Voltage		V_{CES}	1200	V
		Gate-Emitter Voltage		V_{GES}	±20	V
		Collector Current	DC	I_C	8	A
			1ms	I_{CP}	16	
		Collector Power Dissipation (Tc = 25°C)		P_C	80	W
	FRD	Repetitive Peak Reverse Voltage		V_{RRM}	1200	V
		Forward Current	DC	I_F	8	A
			1ms	I_{FM}	16	
Module		Junction Temperature		T_j	150	°C
		Storage Temperature Range		T_{stg}	-40 ~ 125	°C
		Isolation Voltage		V_{Isol}	2500 (AC 1 minute)	V
		Screw Torque		—	3	N·m

Electrical Characteristics (Ta = 25°C)

a. Inverter Stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	±10	μA
Collector Cut-off Current		I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-off Voltage		$V_{GE(off)}$	$I_C = 15mA, V_{CE} = 5V$	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 15A, V_{GE} = 15V$	—	3.00	4.00	V
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0$ $f = 1MHz$	—	1850	—	pF
Switching Time	Turn-on Delay Time	$t_{d(on)}$	Inductive Load $V_{CC} = 600V$ $I_C = 15A$ $V_{GE} = \pm 15V$ $R_G = 100\Omega$ (Note 1)	—	0.08	0.16	μs
	Rise Time	t_r		—	0.12	0.24	
	Turn-on Time	t_{on}		—	0.40	0.80	
	Turn-off Delay Time	$t_{d(off)}$		—	0.30	0.60	
	Fall Time	t_f		—	0.20	0.40	
	Turn-off Time	t_{off}		—	0.70	1.30	
Forward Voltage		V_F	$I_F = 15A, V_{GE} = 0$	—	2.00	2.50	V
Reverse Recovery Time		t_{rr}	$I_F = 15A, V_{GE} = -10V$ $di/dt = 100A/\mu s$	—	0.20	0.50	μs
Thermal Resistance		$R_{th(j-c)}$	Transistor	—	—	1.00	°C/W
			Diode	—	—	1.80	

b. Converter Stage

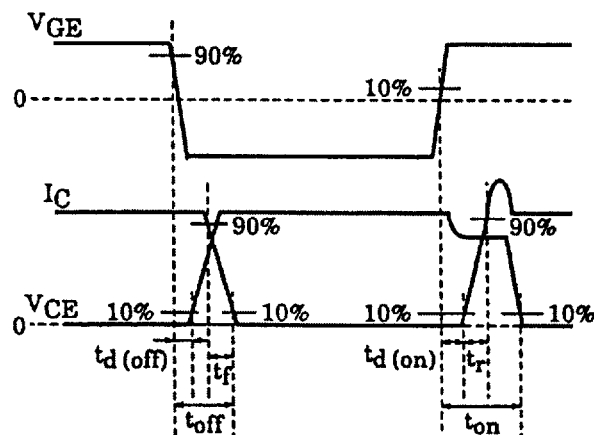
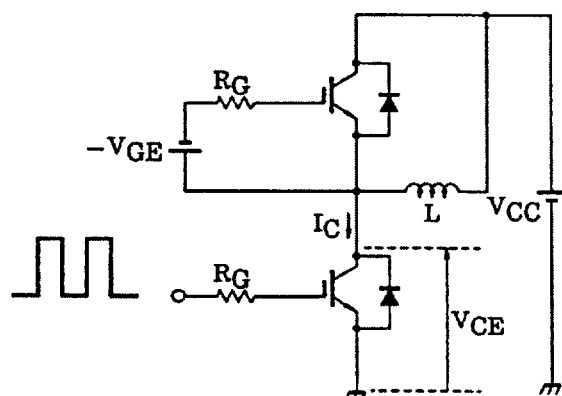
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MX.	UNIT
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 1600V$	—	—	50	μA
Peak Forward Voltage	V_{FM}	$I_{FM} = 15A$	—	1.05	1.20	V
Peak One Cycle Surge Forward Current	I_{FSM}	50Hz Sine-half-wave	250	—	—	A
Thermal Resistance	$R_{th(j-c)}$	—	—	—	2.50	$^{\circ}C/W$

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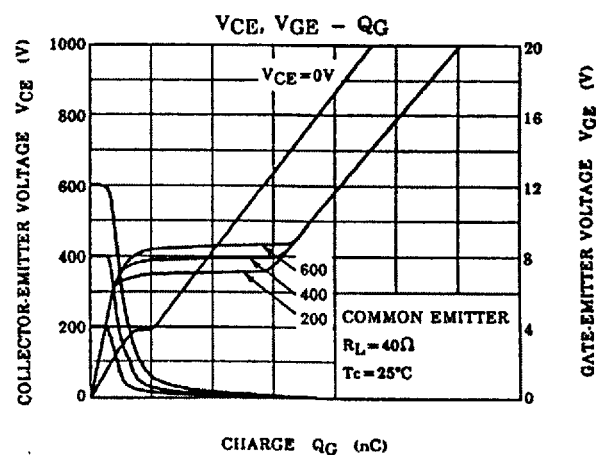
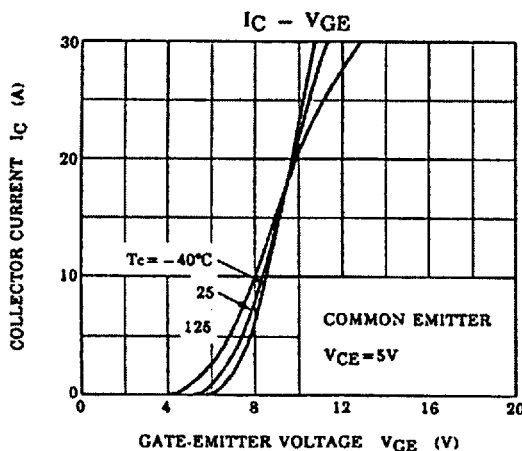
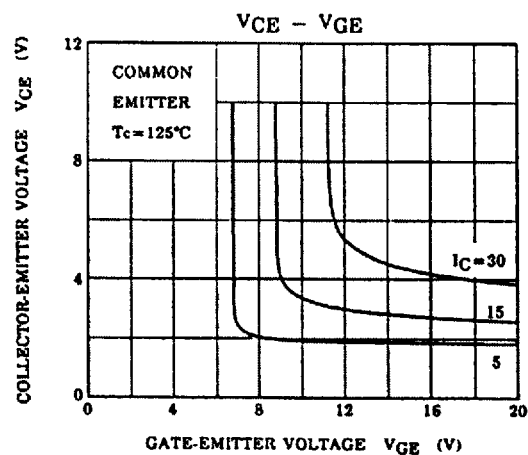
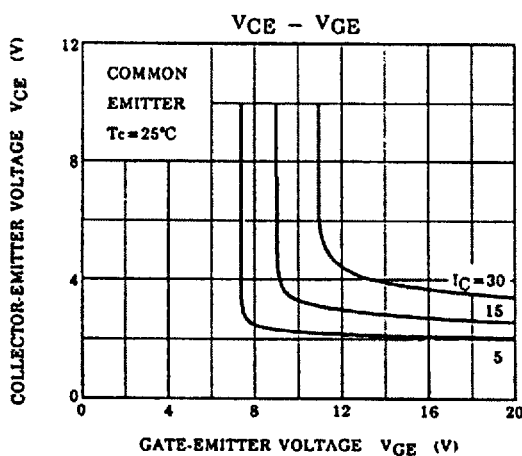
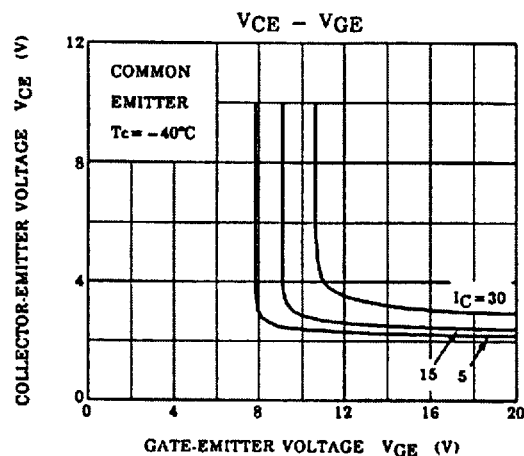
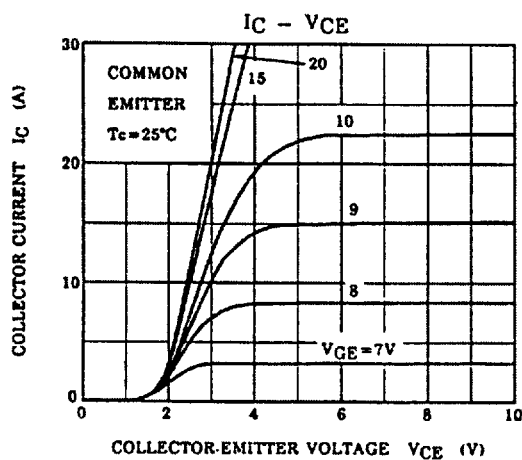
c. Brake Stage

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MX.	UNIT
Gate Leakage Current		I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 10	μA
Collector Cut-off Current		I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	—	—	1.0	mA
Repetitive Peak Reverse Current		I_{RRM}	$V_{RRM} = 1200V$	—	—	1.0	mA
Gate-Emitter Cut-off Voltage		$V_{GE(off)}$	$I_C = 8mA, V_{CE} = 5V$	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 8A, V_{GE} = 15V$	—	3.00	4.00	V
Input Capacitance		C_{ies}	$V_{CE} = 10V, V_{GE} = 0$ $f = 1MHz$	—	1000	—	pF
Switching Time	Turn-on Delay Time	$t_{d(on)}$	Inductive Load $V_{CC} = 600V$ $I_C = 8A$ $V_{GE} = \pm 15V$ $R_G = 150\Omega$ (Note 1)	—	0.08	0.16	μs
	Rise Time	t_r		—	0.12	0.24	
	Turn-on Time	t_{on}		—	0.40	0.80	
	Turn-off Delay Time	$t_{d(off)}$		—	0.30	0.60	
	Fall Time	t_f		—	0.30	0.50	
	Turn-off Time	t_{off}		—	0.70	1.30	
Forward Voltage		V_F	$I_F = 8A, V_{GE} = 0$	—	1.20	2.50	V
Thermal Resistance		$R_{th(j-c)}$	Transistor	—	—	1.56	$^{\circ}C/W$
			Diode	—	—	1.80	

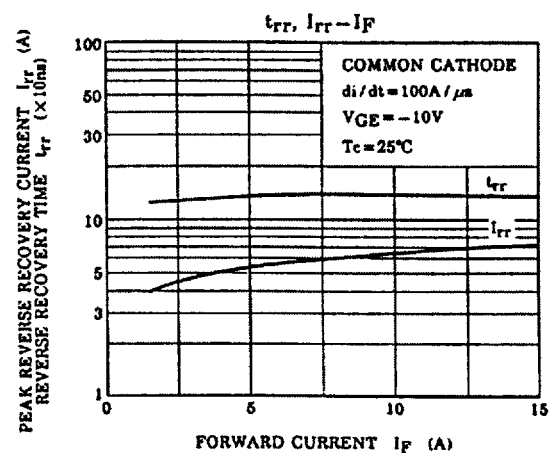
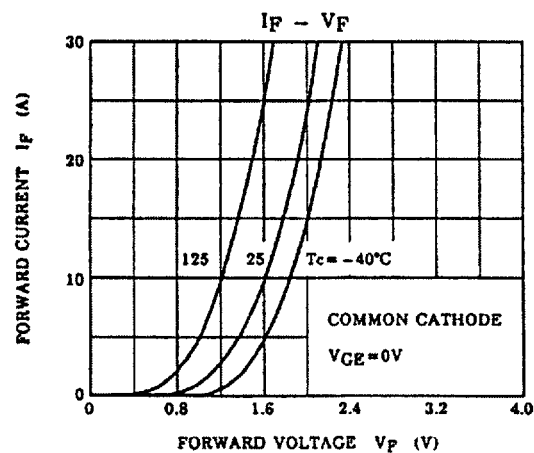
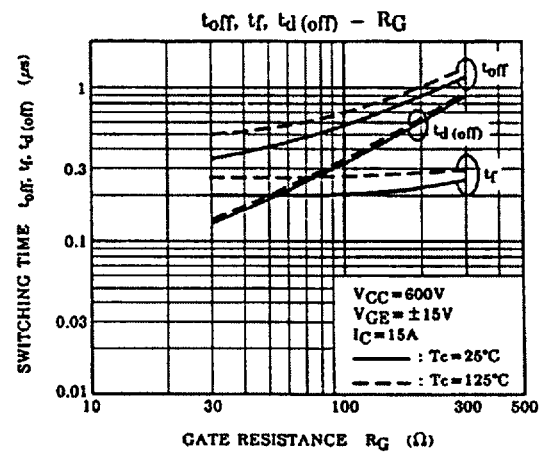
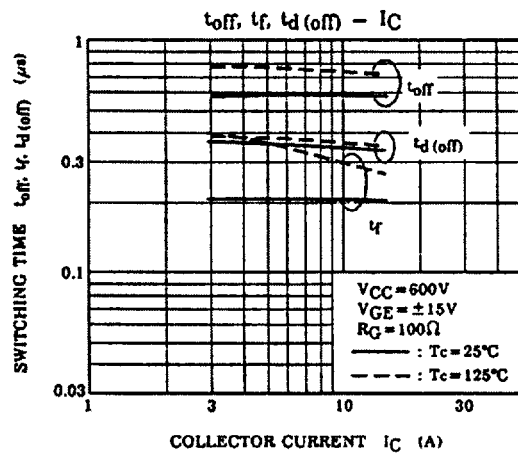
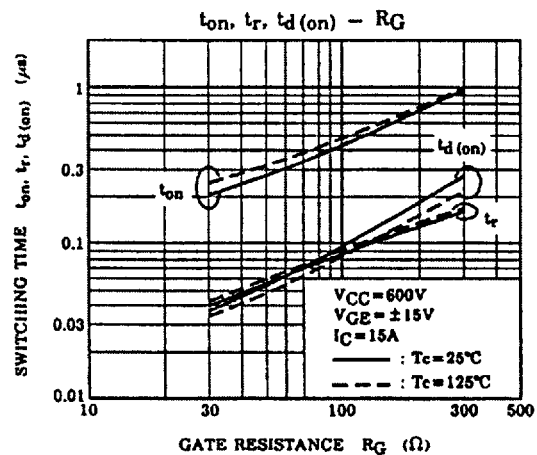
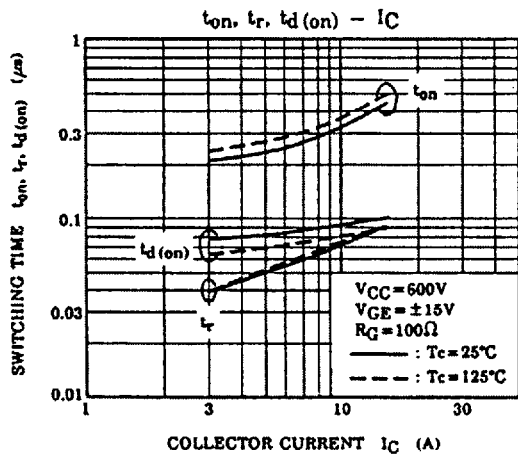
Note. 1 Switching Time Test Circuit & Timing Chart



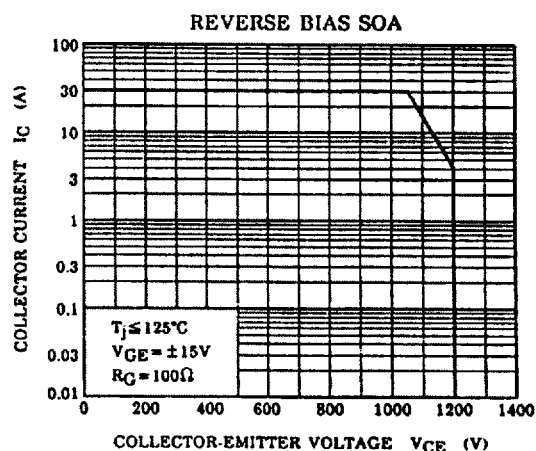
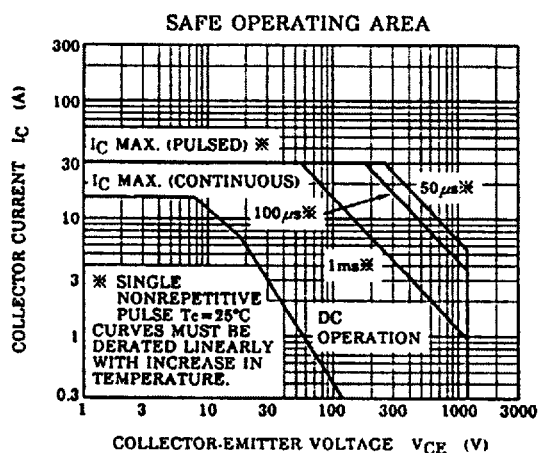
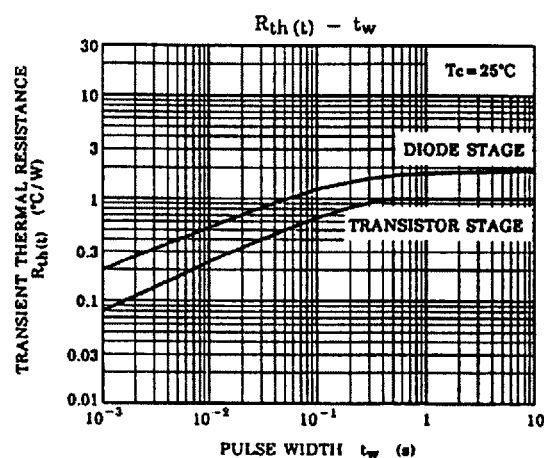
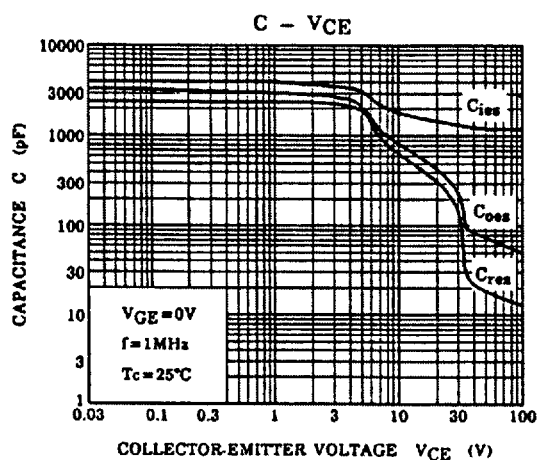
a. Inverter Stage



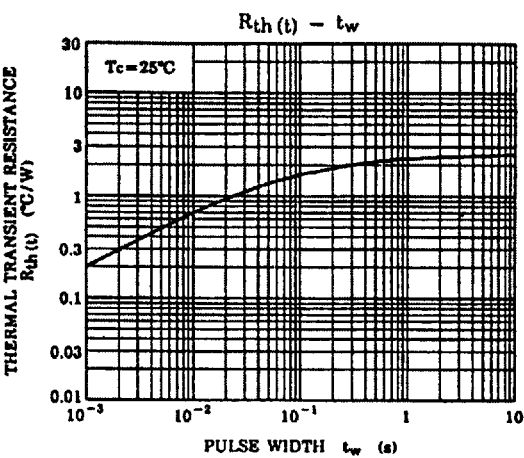
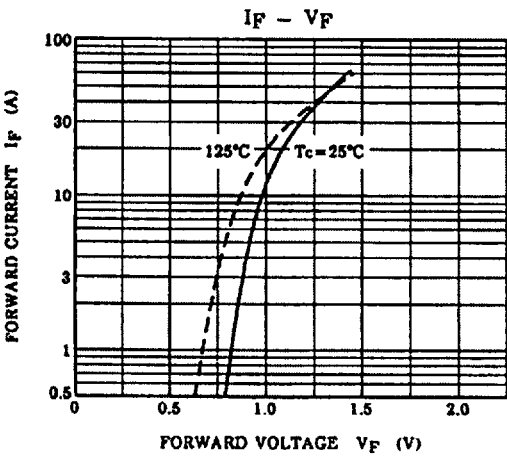
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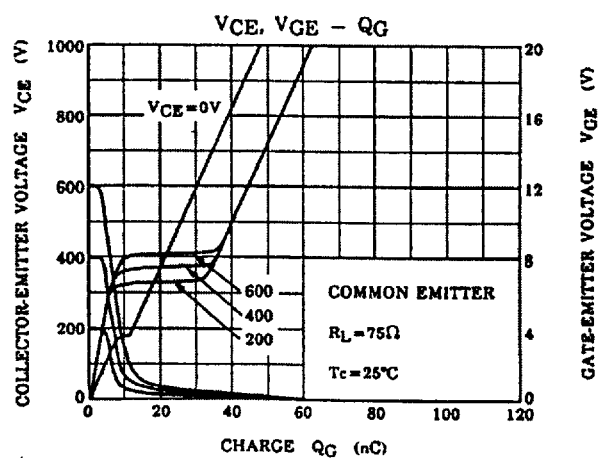
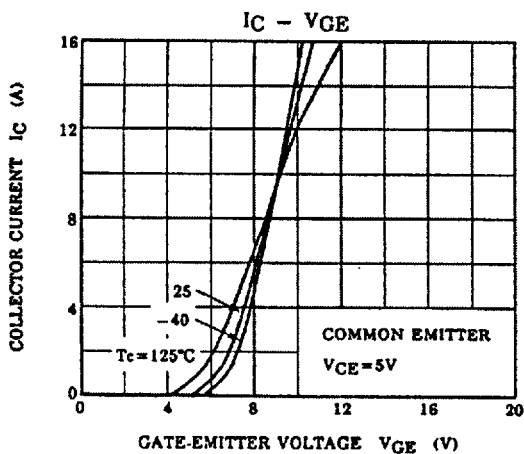
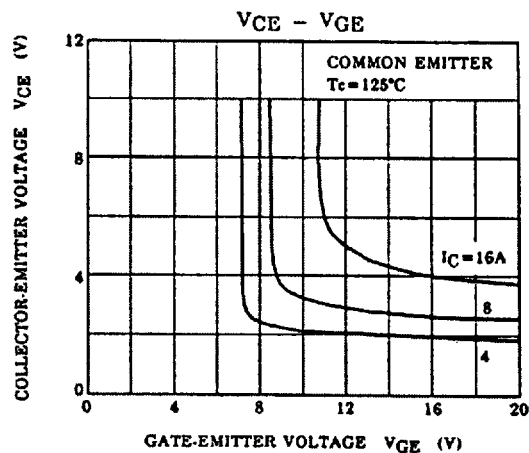
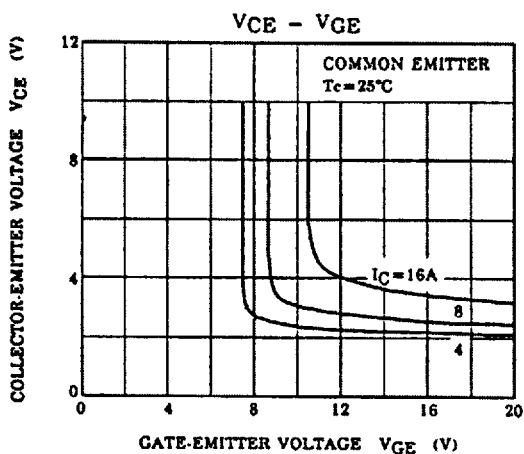
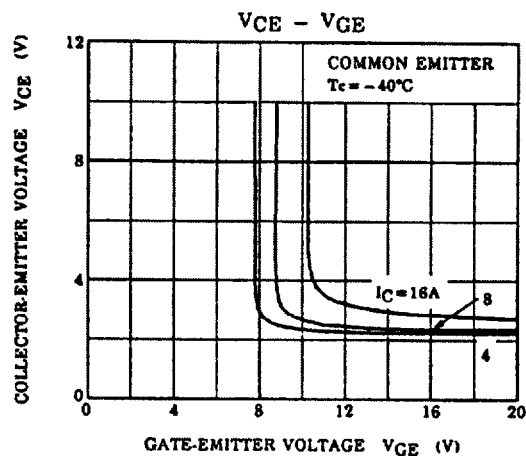
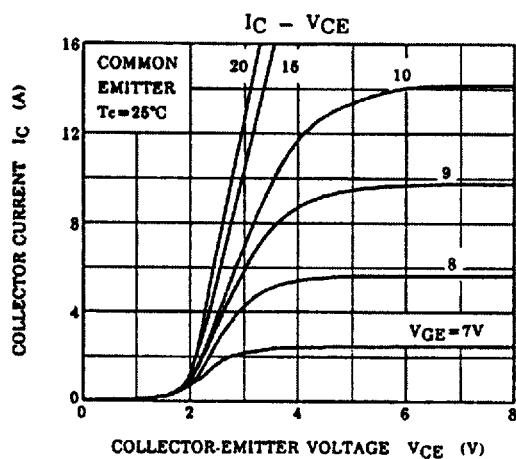
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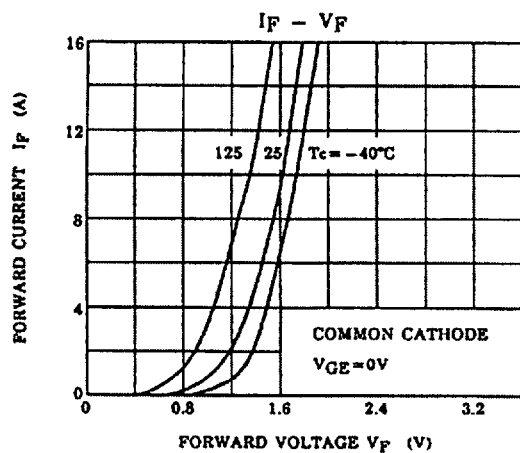
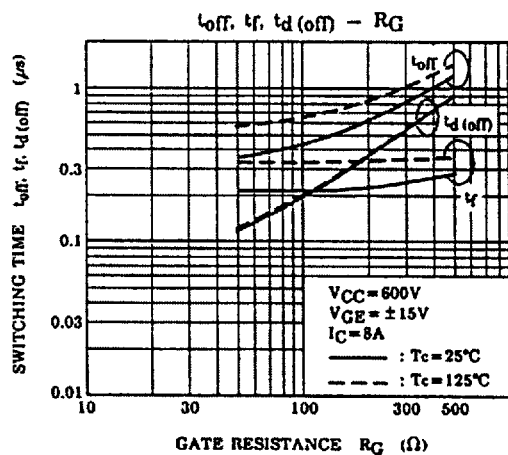
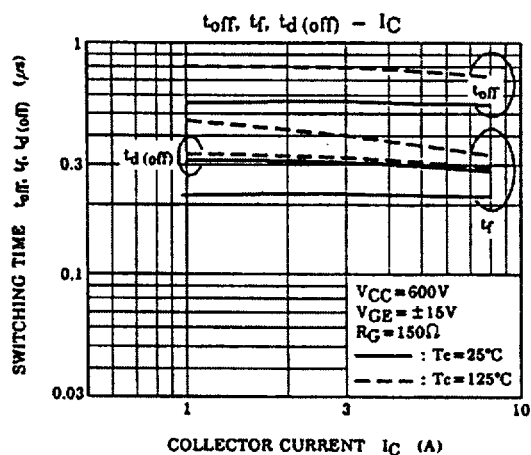
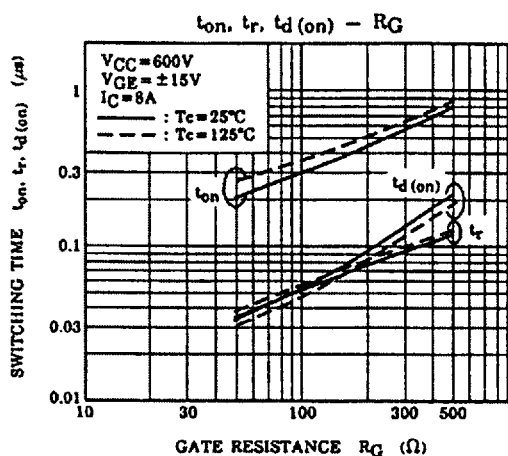
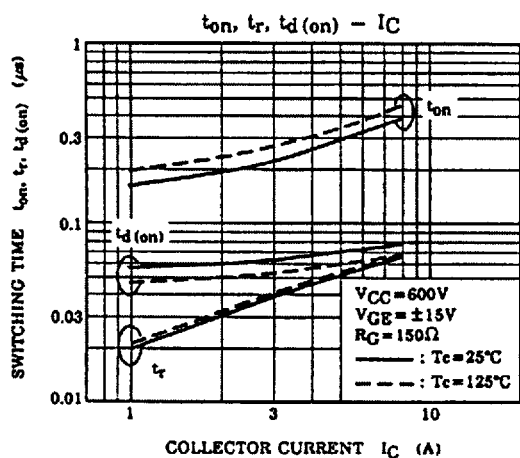
b. Converter Stage



c. Brake Stage



c. Brake Stage



c. Brake Stage

